

**T<sub>c</sub> =25**

	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Drain Current	I <sub>D@TC=25°C</sub>	65	A
	I <sub>D@TC=75°C</sub>	49	A
	I <sub>D@TC=100°C</sub>	41	A
Maximum Drain Current <sup>①</sup>	I <sub>DM</sub>	195	A
Power Dissipation	P <sub>D@TC=25°C</sub>	48	W
Power Dissipation	P <sub>D@TA=25°C</sub>	2.3	W
Junction Temperature	T <sub>J</sub>	-55 to 150	°C
Storage Temperature	T <sub>STG</sub>	-55 to 150	°C
Gate Avalanche Energy (0.1mH)	E <sub>AS</sub>	150	mJ



**Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Thermal					



				1.6		nC
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Note: ① ;

Fig.1 Power Dissipation

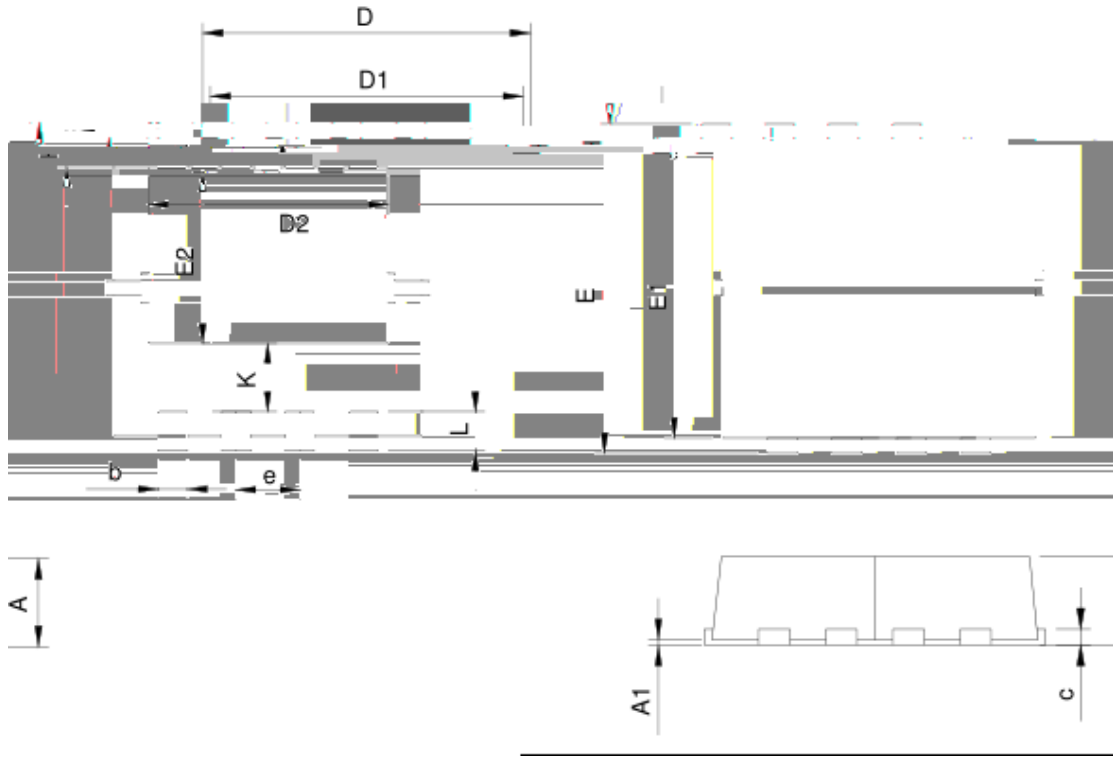
Fig.3 Threshold Voltage V.S Junction Temperature    Fig.4 Resistance V.S Drain Current





I h I -

Unit mm



DFN3.3x3.3-8		RECOMMENDED LAND PATTERN			
		DIMENSIONS		DIMENSIONS	
		MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039	
A1	0.00	0.05	0.000	0.002	
b		0.25	0.35	0.010	
c		0.14	0.20	0.006	
D	3.10	3.50	0.122		
D1	3.05	3.25	0.120		
D2	2.35	2.55	0.093	0.100	
E	3.10	3.50	0.122	0.138	
E1	2.90	3.10	0.114	0.122	
E2	2.90	3.10	0.114	0.122	
e	0.65 BSC	0.52	0.013	0.020	0.026 BSC
H	0.32	0.52	0.013	0.020	
K	0.59	0.79	0.023	0.031	
L	0.25	0.35	0.010	0.022	